

# A 1.6GHz 0.5mW CMOS LC Low Phase Noise VCO Using Bond Wire Inductors

July 30, 1997

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## Outline

- Background and Motivation
- Goals
- Circuit
- Results



# Tradeoffs in Oscillators

## Types

### Relaxation

### Resonant Tank

#### Advantages

simple  
small area  
large tuning range

built-in filter  
low power

#### Disadvantages

phase noise  
power for speed

component tolerance  
component precision  
small tuning range



## Type of Inductor

### Bond wire vs. Spiral

- less precision in value
- lower parasitic capacitance
- less die area
- higher Q



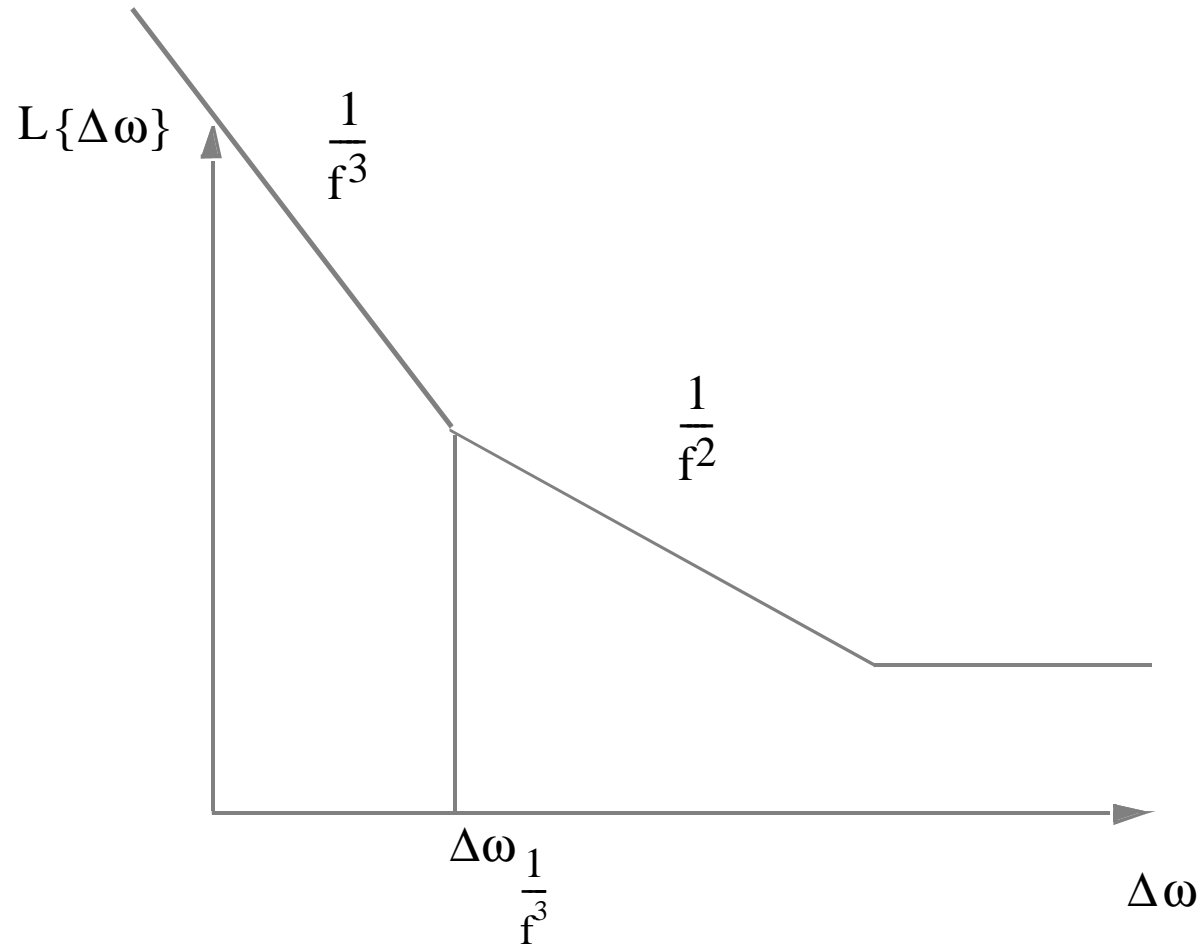
## Goals of Design

- 1.6GHz (GPS)
- Low Power
- Minimum Phase Noise
- Tunable
- Reasonable Area



# Typical Phase Noise Plot

Phase Noise (dBc/Hz)



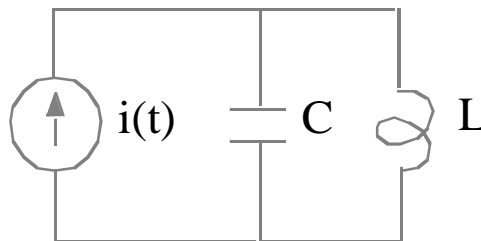
Frequency offset from carrier (rad/s)



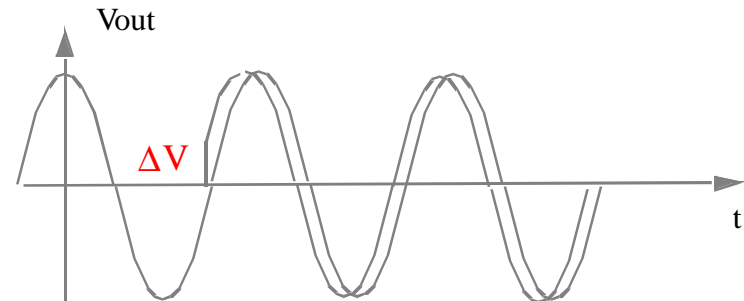
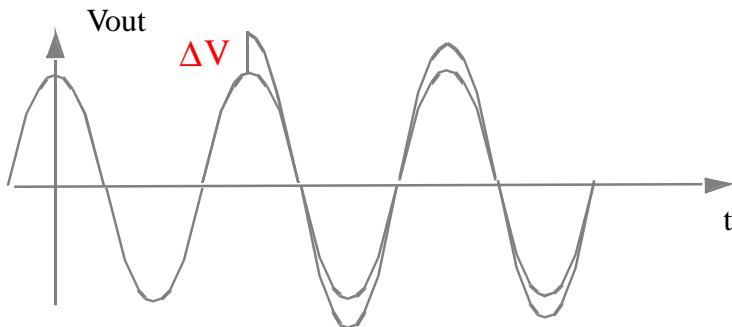
# Hajimiri Phase Noise Model

Impulse injection:

At peak



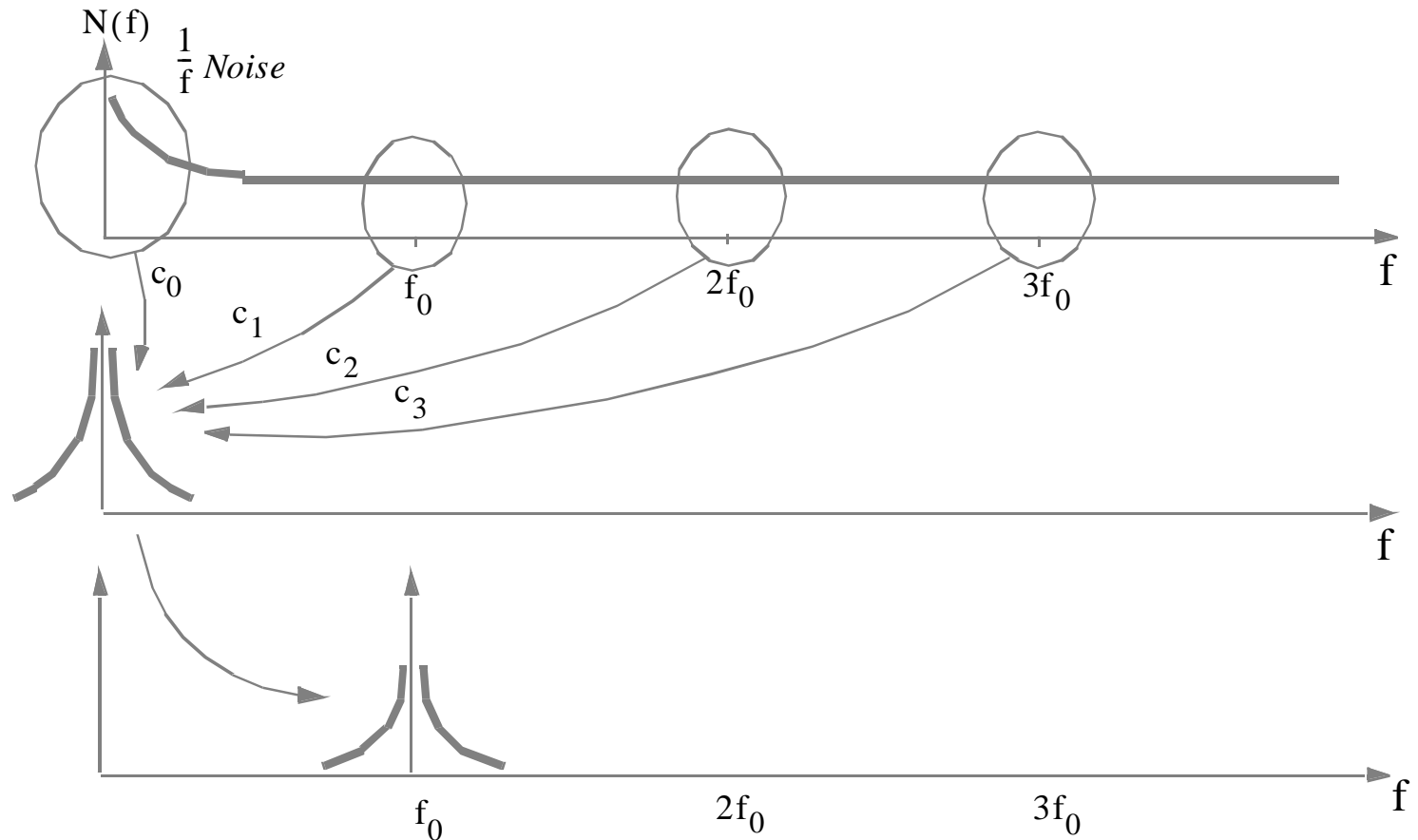
At zero crossing



Oscillators are Linear Time-Variant Systems



# Hajimiri Phase Noise Model



Conversion of noise to phase fluctuations  
and phase noise sidebands





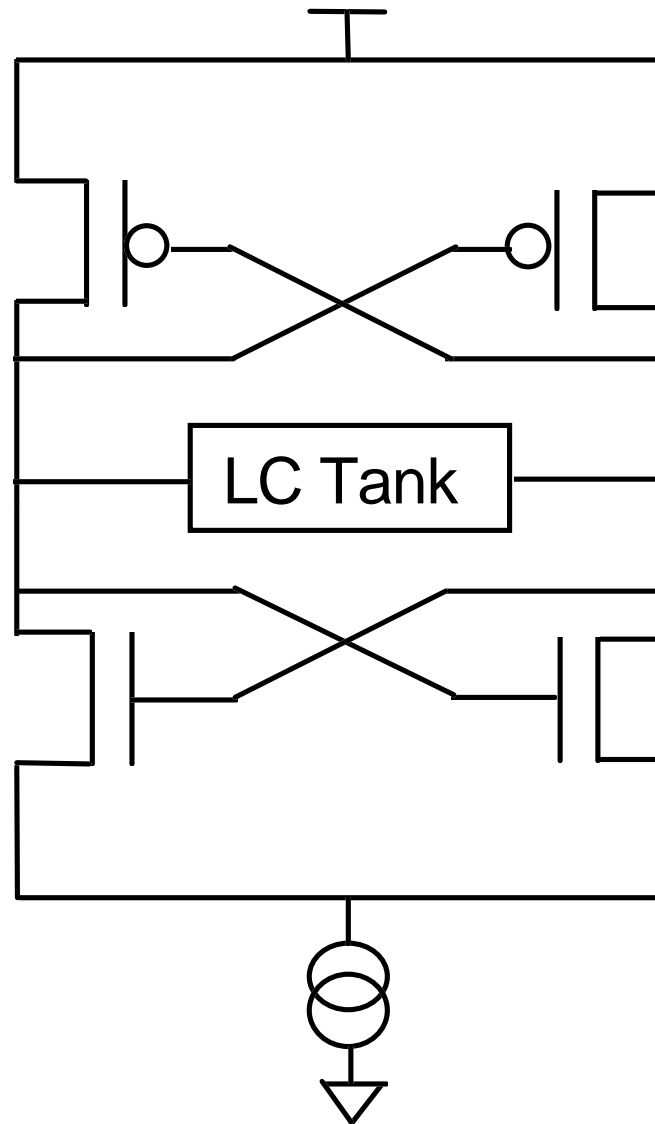
## How To Achieve Low Phase Noise

- More Power
- Higher Q Resonant Tank
- Single-ended Symmetry



# Basic Design Configuration

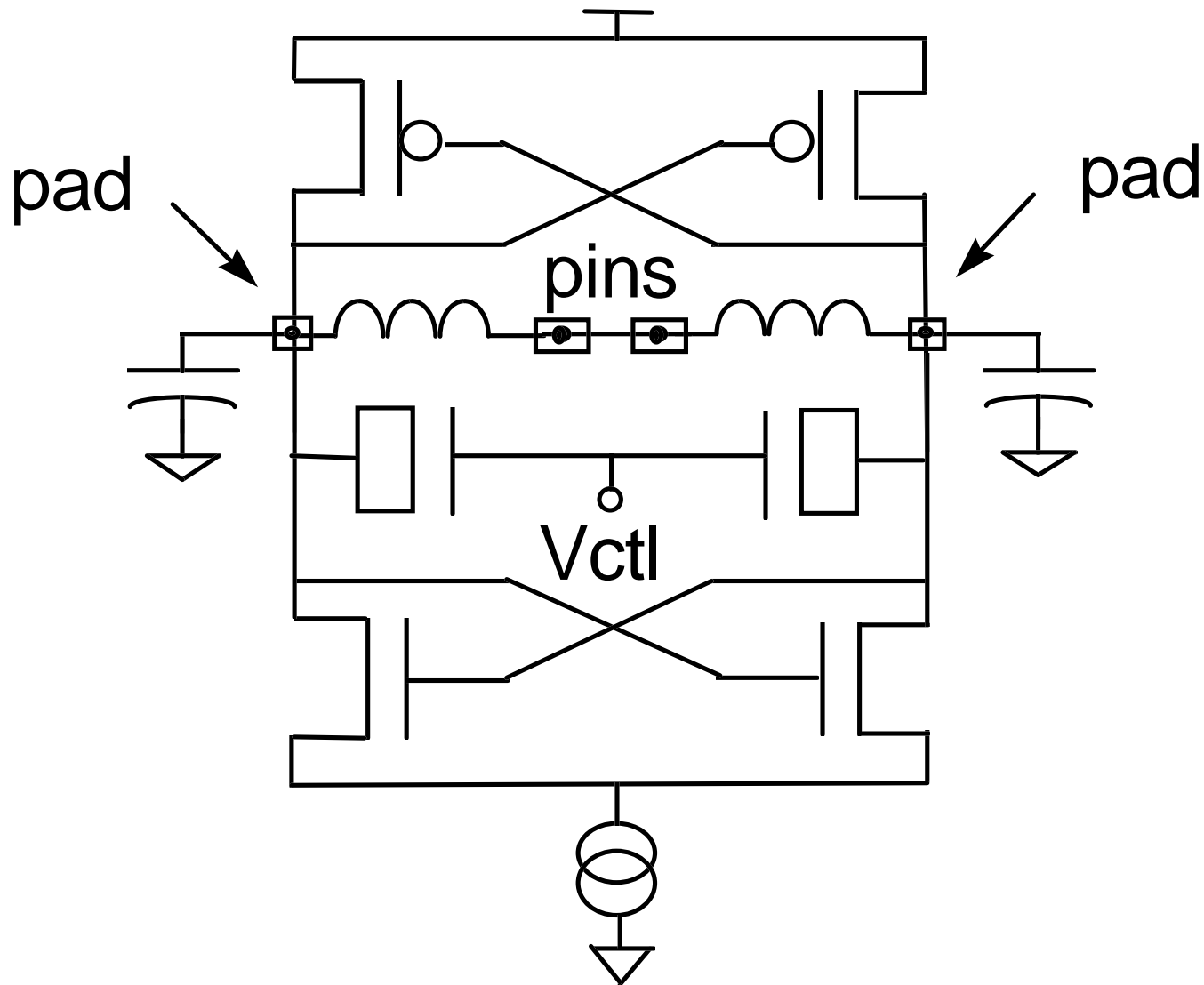
$$W_p = 2 \times W_n$$





## A 0.5mW, 1.6GHz CMOS LC Low Phase Noise VCO using Bond Wires

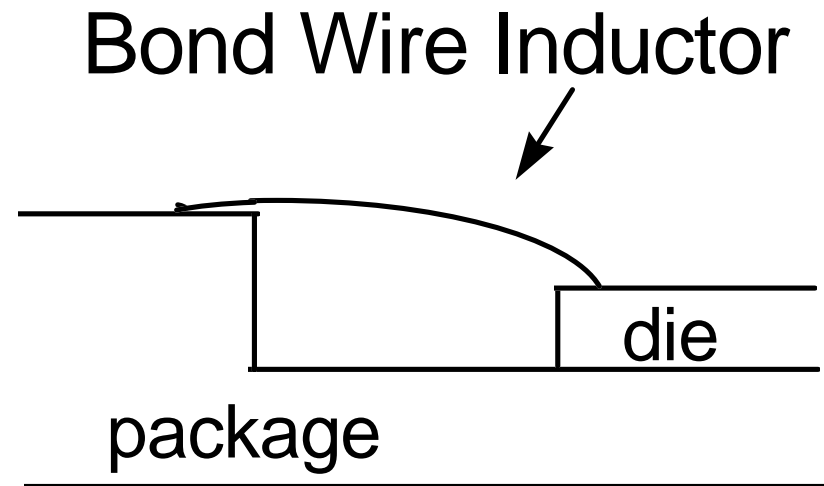
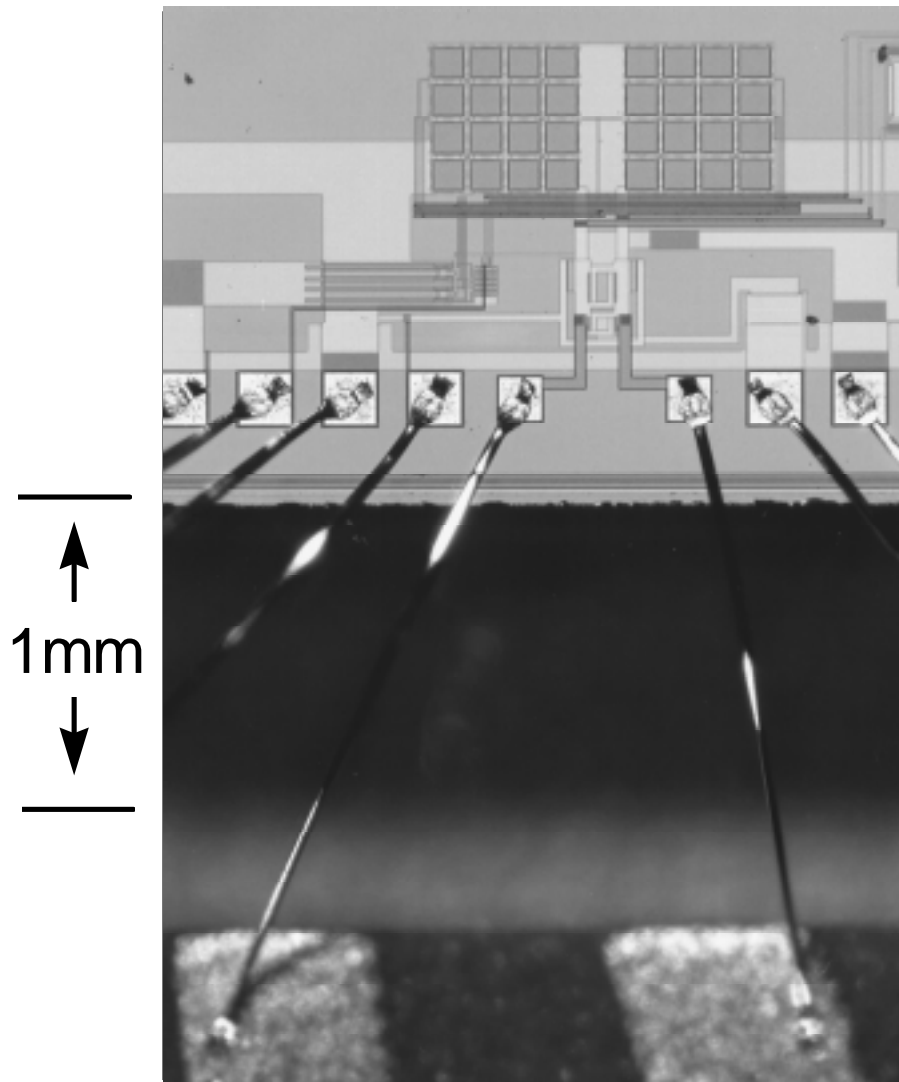
# Circuit Diagram





A 0.5mW, 1.6GHz CMOS LC Low Phase Noise VCO using Bond Wires

# Die Photo and Packaging





## A 0.5mW, 1.6GHz CMOS LC Low Phase Noise VCO using Bond Wires

# Results

Frequency	1.6GHz
Power	0.5mW at 2.0V supply
Phase Noise	-95dBc/Hz (100kHz offset)
Tuning Range	130MHz
Process Technology	0.5- $\mu$ m MOSIS standard CMOS



## A 0.5mW, 1.6GHz CMOS LC Low Phase Noise VCO using Bond Wires

# Figure of Merit at 100kHz offset

<u>Technology</u>	<u>Frequency</u>	<u>Power</u>	<u>Phase Noise @100kHz</u>	<u>FOM</u>
[7] Bipolar	1.6GHz	3mW	-95.1dBc/Hz	212dB
CMOS	1.6GHz	0.5mW	-95dBc/Hz	220dB

Figure of Merit =  $10 \log (\text{Freq}/(\text{Phase Noise} \times \text{Power}))$



## A 0.5mW, 1.6GHz CMOS LC Low Phase Noise VCO using Bond Wires

# Figure of Merit at 10kHz offset

<u>Technology</u>	<u>Frequency</u>	<u>Power</u>	<u>Phase Noise</u> <u>@10kHz</u>	<u>FOM</u>
<b>[5] Bipolar</b>	<b>1.13GHz</b>	<b>2mW</b>	<b>-75dBc/Hz</b>	<b>192.5dB</b>
<b>CMOS</b>	<b>1.6GHz</b>	<b>0.5mW</b>	<b>-64dBc/Hz</b>	<b>189dB</b>

Figure of Merit =  $10 \log (\text{Freq}/(\text{Phase Noise} \times \text{Power}))$



## Conclusions

- Bond wires offer a high quality monolithic inductance.
- The Hajimiri Phase Noise model provides methods to minimize close-in phase noise in oscillators.
- CMOS is a growing and attractive solution for RF oscillators.





## Acknowledgements

For their various contributions, the authors would like to thank:

- Rafael J. Betancourt-Zamora
- David M. Colleran
- Robert W. Dutton
- Derek K. Shaeffer
- Maria Perea
- Michael A. Swartwout
- Leah K. Meagher